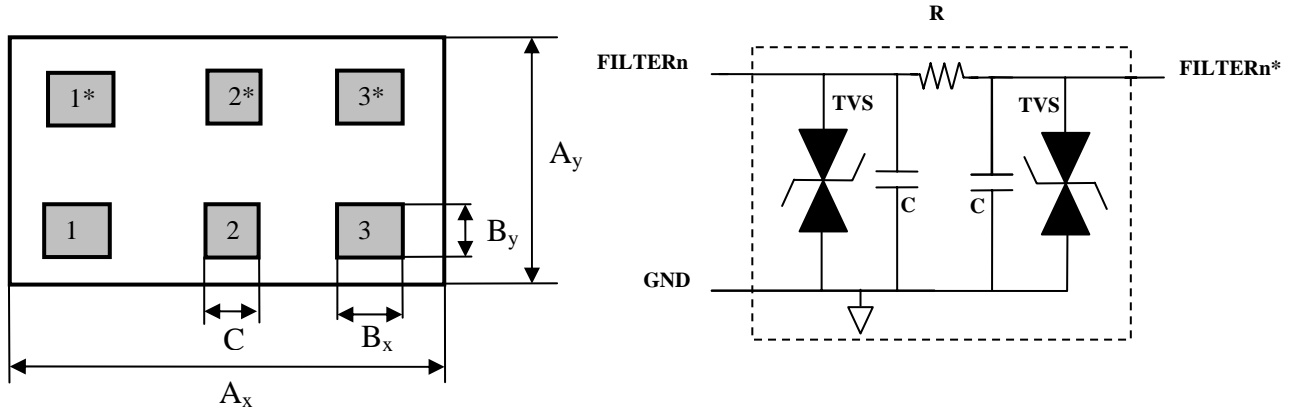


## EMI-602M1

### 2 Channel EMI/RFI Filter Array with ESD Protection for Microphone Ports.



**Mechanical date:**  $A_x = 800\mu\text{m}$ ,  $A_y = 470\mu\text{m}$ .  
 $B_x = 120\mu\text{m}$ ,  $B_y = 97\mu\text{m}$   
 $C_x = C_y = 103\mu\text{m}$

**Schematic and pinning diagram.**

**Chip thickness:**  $138 \pm 12\mu\text{m}$ .

**Scribe Line width** -  $60\mu\text{m}$ .

**Top Metal:** Al – for wire bonding.

**Back side:** Ti-Ni-Ag for soldering.

**Pin 2&2\*-GND**

### Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	$V_{RWM}$	-	5	V
Electrostatic Discharge	$V_{ESD}$	IEC 61000-4-2, level 4	$\pm 10$ (Contact); $\pm 16$ (Air)	kV
Max. junction temperature	$T_J$	-	125	$^{\circ}\text{C}$

### Characteristics ( $T_j = 25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{BR}$	Breakdown voltage	$I_R = 1\text{mA}$	6,02	-	9,0	V
$I_R$	Diode reverse leakage current	$V = 5\text{V}$	-	-	4	$\mu\text{A}$
$V_f$	Diode Forward Voltage	$I_f = 10\text{mA}$	-	0.8	1.0	V
R	Resistance	-	8,5	10	11,5	Ohm
$C_{in}$	Capacitance	$V_R = 2.5\text{V}$ , $f = 1\text{MHz}$			160	pF

\*- For Device testing.